INTEGRATED CIRCUITS

DATA SHEET

74AHC1G32; 74AHCT1G32 2-input OR gate

Product specification Supersedes data of 2002 Mar 26 2002 Jun 05





Philips Semiconductors

2-input OR gate

74AHC1G32; 74AHCT1G32

FEATURES

- Symmetrical output impedance
- · High noise immunity
- ESD protection:
 - HBM EIA/JESD22-A114-A exceeds 2000 V
 - MM EIA/JESD22-A115-A exceeds 200 V
 - CDM EIA/JESD22-C101 exceeds 1000 V.
- · Low power dissipation
- · Balanced propagation delays
- Multiple very small 5-pin packages
- · Output capability: standard
- Specified from -40 to +125 °C.

DESCRIPTION

The 74AHC1G/AHCT1G32 is a high-speed Si-gate CMOS device.

The 74AHC1G/AHCT1G32 provides the 2-input OR function.

QUICK REFERENCE DATA

GND = 0 V; T_{amb} = 25 °C; t_r = $t_f \le 3.0$ ns.

SYMBOL	PARAMETER	CONDITIONS	TYP	UNIT	
STWIBOL	PARAMETER	CONDITIONS	AHC1G	AHCT1G	UNIT
t _{PHL} /t _{PLH}	propagation delay A and B to Y	C _L = 15 pF; V _{CC} = 5 V	3.2	3.3	ns
C _I	input capacitance		1.5	1.5	pF
C _{PD}	power dissipation capacitance	C _L = 50 pF; f = 1 MHz; notes 1 and 2	16	17	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i + (C_L \times V_{CC}^2 \times f_o)$$
 where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

 V_{CC} = supply voltage in Volts.

2. $V_I = GND$ to V_{CC} .

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FUNCTION TABLE

See note 1.

INP	UTS	OUTPUT						
Α	A B							
L	L	L						
L	Н	Н						
Н	L	Н						
Н	Н	Н						

Note

1. H = HIGH voltage level;

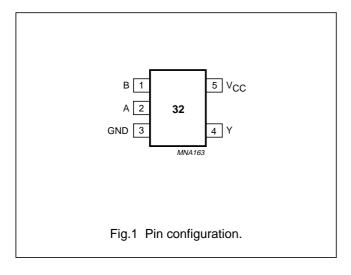
L = LOW voltage level.

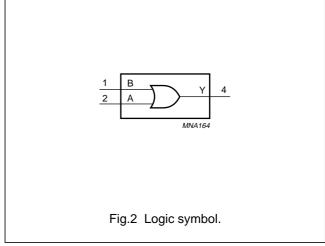
ORDERING INFORMATION

TYPE NUMBER	TEMPERATURE	PACKAGE								
I TPE NUMBER	RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING				
74AHC1G32GW	-40 to +125 °C	5	SC-88A	plastic	SOT353	AG				
74AHCT1G32GW	−40 to +125 °C	5	SC-88A	plastic	SOT353	CG				
74AHC1G32GV	-40 to +125 °C	5	SC-74A	plastic	SOT753	A32				
74AHCT1G32GV	-40 to +125 °C	5	SC-74A	plastic	SOT753	C32				

PINNING

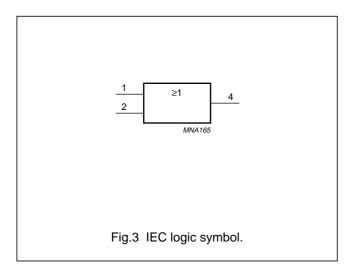
PIN	SYMBOL	DESCRIPTION
1	В	data input B
2	A	data input A
3	GND	ground (0 V)
4	Υ	data output Y
5	V _{CC}	supply voltage

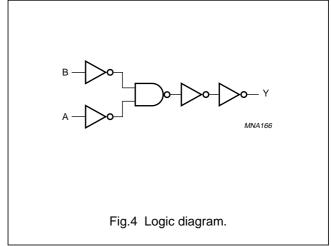




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RECOMMENDED OPERATING CONDITIONS

CVMPOL	DADAMETED	CONDITIONS	7	4AHC1	G	7	4AHCT1	IG	LINUT
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	UNIT
V _{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	٧
VI	input voltage		0	_	5.5	0	_	5.5	V
Vo	output voltage		0	_	V _{CC}	0	_	V _{CC}	V
T _{amb}	operating ambient temperature	see DC and AC characteristics per device	-40	+25	+125	-40	+25	+125	°C
t _r , t _f	input rise and fall	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	_	_	100	_	_	_	ns/V
	times	$V_{CC} = 5 \pm 0.5 \text{ V}$	_	_	20	_	_	20	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I _{IK}	input diode current	$V_1 < -0.5 \text{ V}$	_	-20	mA
I _{OK}	output diode current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}; \text{ note 1}$	_	±20	mA
Io	output source or sink current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	_	±25	mA
I _{CC}	V _{CC} or GND current		_	±75	mA
T _{stg}	storage temperature		-65	+150	°C
P_D	power dissipation per package	for temperature range from -40 to +125 °C	_	250	mW

Note

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

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DC CHARACTERISTICS

Family 74AHC1G

Over recommended operating conditions; voltages are referenced to GND (ground = 0 V).

	TEST CONDITIONS T _{amb} (°C)							C)			
SYMBOL	PARAMETER	OTLIED	V _{CC}		25		−40 t	o +85	-40 to	+125	UNIT
		OTHER	(V)	MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.	
V _{IH}	HIGH-level input		2.0	1.5	_	_	1.5	-	1.5	_	٧
	voltage		3.0	2.1	-	_	2.1	_	2.1	_	V
			5.5	3.85	_	_	3.85	_	3.85	_	V
V_{IL}	LOW-level input		2.0	_	_	0.5	_	0.5	_	0.5	V
	voltage		3.0	_	_	0.9	_	0.9	_	0.9	V
			5.5	_	_	1.65	_	1.65	_	1.65	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = -50 \mu\text{A}$	2.0	1.9	2.0	_	1.9	_	1.9	_	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = -50 \mu\text{A}$	3.0	2.9	3.0	_	2.9	_	2.9	_	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = -50 \mu\text{A}$	4.5	4.4	4.5	-	4.4	-	4.4	-	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = -4.0 \text{ mA}$	3.0	2.58	_	_	2.48	_	2.40	_	V
		$V_I = V_{IH}$ or V_{IL} ; $I_O = -8.0$ mA	4.5	3.94	_	-	3.8	_	3.70	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 50 \mu\text{A}$	2.0	_	0	0.1	_	0.1	_	0.1	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 50 \mu\text{A}$	3.0	_	0	0.1	_	0.1	_	0.1	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 50 \mu\text{A}$	4.5	_	0	0.1	_	0.1	_	0.1	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 4.0 \text{ mA}$	3.0	_	_	0.36	_	0.44	_	0.55	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 8.0 \text{ mA}$	4.5	_	_	0.36	_	0.44	_	0.55	V
I _{LI}	input leakage current	$V_I = V_{CC}$ or GND	5.5	-	_	0.1	_	1.0	_	2.0	μΑ
I _{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	5.5	_	_	1.0	_	10	_	40	μΑ
Cı	input capacitance			_	1.5	10	_	10	_	10	pF

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Family 74AHCT1G

Over recommended operating conditions; voltages are referenced to GND (ground = 0 V).

		TEST CONDI	TIONS			Т	amb (°(C)			
SYMBOL	PARAMETER	OTHER	V 00		25		−40 t	o +85	-40 to	+125	UNIT
		OTHER	V _{CC} (V)	MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.	
V _{IH}	HIGH-level input voltage		4.5 to 5.5	2.0	_	_	2.0	_	2.0	_	V
V _{IL}	LOW-level input voltage		4.5 to 5.5	_	_	0.8	_	0.8	_	0.8	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = -50 \mu\text{A}$	4.5	4.4	4.5	_	4.4	_	4.4	_	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = -8.0 \text{ mA}$	4.5	3.94	_	_	3.8	_	3.70	_	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 50 \mu\text{A}$	4.5	_	0	0.1	_	0.1	_	0.1	V
		$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 8.0 \text{ mA}$	4.5	_	_	0.36	_	0.44	_	0.55	V
ILI	input leakage current	$V_I = V_{IH}$ or V_{IL}	5.5	_	_	0.1	_	1.0	_	2.0	μΑ
I _{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	5.5	_	_	1.0	_	10	_	40	μΑ
Δl _{CC}	additional quiescent supply current per input pin	$V_I = 3.4 \text{ V};$ other inputs at V_{CC} or GND; $I_O = 0$	5.5	_	_	1.35	-	1.5	-	1.5	mA
C _I	input capacitance			_	1.5	10	_	10	_	10	pF

2-input OR gate

74AHC1G32; 74AHCT1G32

AC CHARACTERISTICS

Type 74AHC1G32

 $GND = 0 \ V; \ t_r = t_f \leq 3.0 \ ns.$

		TEST CONDITI			7	_{amb} (°C	;)				
SYMBOL	PARAMETER				25		−40 t	o +85	−40 to	+125	UNIT
		WAVEFORMS	C _L (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.	
V _{CC} = 3.0	CC = 3.0 to 3.6 V; note 1										
t _{PHL} /t _{PLH}	propagation delay	see Figs 5 and 6	15	_	4.4	7.9	1.0	9.5	1.0	10.0	ns
	A and B to Y		50	_	6.3	11.4	1.0	13.0	1.0	14.5	ns
V _{CC} = 4.5	to 5.5 V; note 2							•			
t _{PHL} /t _{PLH}	propagation delay	see Figs 5 and 6	15	_	3.2	5.5	1.0	6.5	1.0	7.0	ns
	A and B to Y		50	_	4.6	7.5	1.0	8.5	1.0	9.5	ns

Notes

- 1. All typical values are measured at V_{CC} = 3.3 V.
- 2. All typical values are measured at V_{CC} = 5.0 V.

Type 74AHCT1G32

 $GND = 0 \ V; \ t_r = t_f \leq 3.0 \ ns.$

		TEST CONDITI	T _{amb} (°C)								
SYMBOL	PARAMETER	WAVEFORMS C _L		AVETORMS CL 25			−40 t	o +85	-40 to +125		UNIT
		VVAVEFORIVIS	(pF)	MIN.	MIN. TYP. MAX		MIN.	MAX.	MIN.	MAX.	
V _{CC} = 4.5	to 5.5 V; note 1										
t _{PHL} /t _{PLH}	propagation delay	see Figs 5 and 6	15	_	3.3	6.9	1.0	8.0	1.0	9.0	ns
	A and B to Y		50	_	4.8	7.9	1.0	9.0	1.0	10	ns

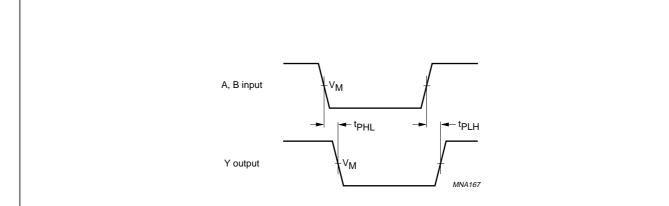
Note

1. All typical values are measured at V_{CC} = 5.0 V.

2-input OR gate

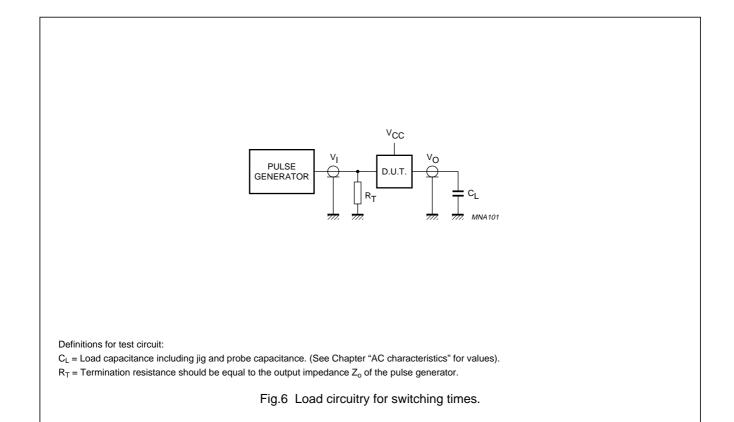
74AHC1G32; 74AHCT1G32

AC WAVEFORMS



FAMILY	V _I INPUT REQUIREMENTS	V _M INPUT	V _M OUTPUT
AHC1G	GND to V _{CC}	50% V _{CC}	50% V _{CC}
AHCT1G	GND to 3.0 V	1.5 V	50% V _{CC}

Fig.5 The input (A and B) to output (Y) propagation delays.



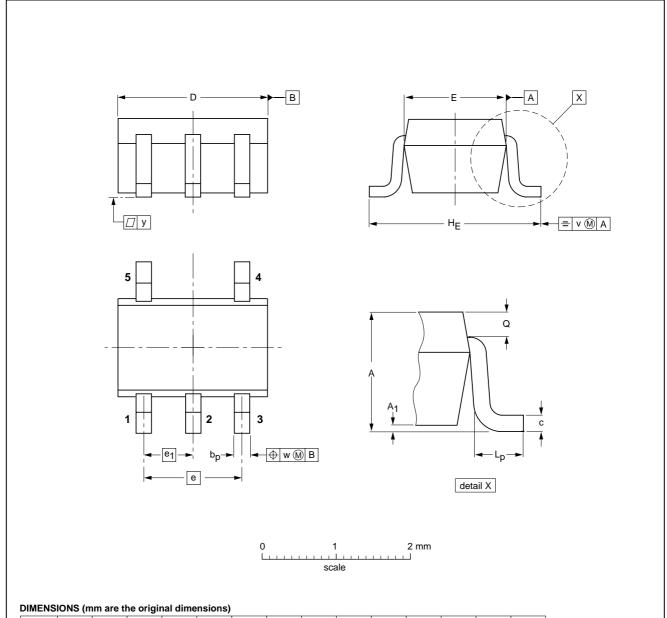
2-input OR gate

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PACKAGE OUTLINES

Plastic surface mounted package; 5 leads

SOT353



UNIT	Α	A ₁ max	bp	С	D	E ⁽²⁾	е	e ₁	HE	Lp	Q	v	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE	REFERENCES				EUROPEAN	ICCUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT353			SC-88A			97-02-28

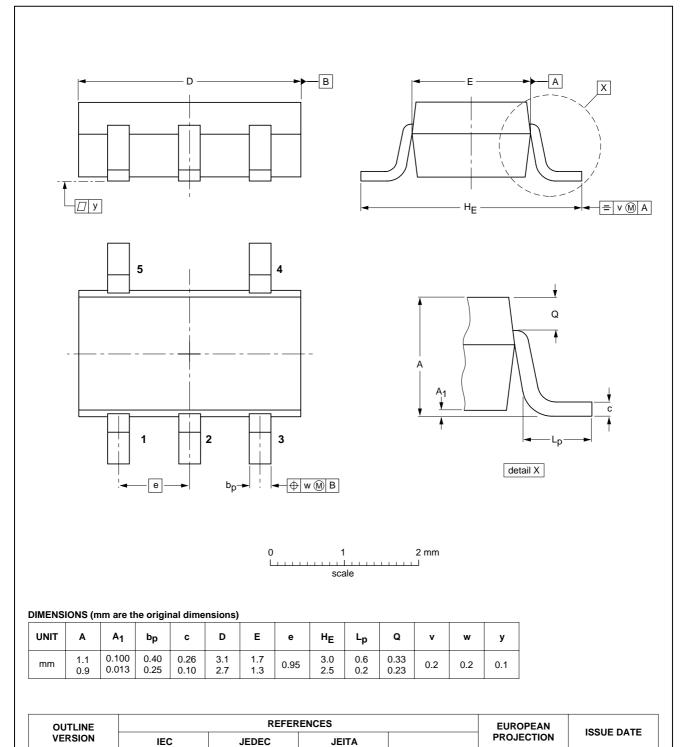
2-input OR gate

74AHC1G32; 74AHCT1G32

02-04-16

Plastic surface mounted package; 5 leads

SOT753



SC-74A

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SOT753

2-input OR gate

74AHC1G32; 74AHCT1G32

SOLDERING

Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our "Data Handbook IC26; Integrated Circuit Packages" (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 220 °C for thick/large packages, and below 235 °C for small/thin packages.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

 For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to $300\ ^{\circ}$ C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 $^{\circ}$ C.

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Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE ⁽¹⁾	SOLDERING METHOD		
PACKAGE	WAVE	REFLOW ⁽²⁾	
BGA, LBGA, LFBGA, SQFP, TFBGA, VFBGA	not suitable	suitable	
HBCC, HBGA, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable ⁽³⁾	suitable	
PLCC ⁽⁴⁾ , SO, SOJ	suitable	suitable	
LQFP, QFP, TQFP	not recommended ⁽⁴⁾⁽⁵⁾	suitable	
SSOP, TSSOP, VSO	not recommended ⁽⁶⁾	suitable	

Notes

- 1. For more detailed information on the BGA packages refer to the "(LF)BGA Application Note" (AN01026); order a copy from your Philips Semiconductors sales office.
- 2. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 3. These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- 4. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 5. Wave soldering is suitable for LQFP, TQFP and QFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 6. Wave soldering is suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

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DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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NOTES

2-input OR gate

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NOTES

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Contact information

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